AMENDMENTS TO THE CLAIMS:

The listing of claims will replace all prior versions, and listings of claims in the application:

LISTING OF THE CLAIMS

1. (Currently Amended) An improved phosphor film for a thick film dielectric electroluminescent display, said phosphor film selected from the group consisting of

(a) a rare earth activated alkaline earth ~~thioaluminate~~ phosphor having the formula AB_xC_y:RE wherein;

A is selected from one or more of the group consisting of Mg, Ca, Sr and Ba;

B is selected from one or more of the group consisting of Al, Ga and In;

C is selected from one or more of the group consisting of S and Se; and RE is a rare earth activator species;

(b) a rare earth or transition metal activated zinc selenide; and

(c) a rare earth or transition metal activated zinc sulfo-selenide,

wherein said phosphor film of (a), (b) and (c) is provided with an aluminum nitride barrier layer on a top and/or bottom side of the phosphor film.

2. (Currently Amended) The phosphor film of claim 1, wherein said rare earth activated alkaline earth phosphor comprises a thioaluminate phosphor ~~has the formula AB_xC_y:RE wherein;~~

~~A is selected from one or more of the group consisting of Mg, Ca, Sr and Ba;~~

~~B is selected from one or more of the group consisting of Al, Ga and In;~~

~~C is selected from one or more of the group consisting of S and Se; and RE is a rare earth activator species~~.

3. (Previously Presented) The phosphor film of claim 2, wherein C may also include oxygen at a relative atomic concentration that is less than 0.2 of the combined S and Se concentrations.

4. (Previously Presented) The phosphor film of claim 2, wherein RE is selected from the group consisting of Eu and Ce.

5. (Previously Presented) The phosphor film of claim 1, wherein said aluminum nitride barrier layer is provided on top of said phosphor of (a) to (c).

6. (Previously Presented) The phosphor film of claim 1, wherein said aluminum nitride barrier layer is provided on the bottom of said phosphor of (a), (b), and (c).

7. (Previously Presented) The phosphor of claim 1, wherein said aluminum nitride barrier layer is provided on the top and bottom of said phosphor of (a) to (c).

8. (Previously Presented) The phosphor of claim 1, wherein said aluminum nitride barrier layer is about 30nm to about 50nm thick.

9. (Previously Presented) The phosphor of claim 8, wherein said aluminum nitride barrier layer is deposited by sputtering.

10. (Previously Presented) The phosphor of claim 9, wherein said sputtering is conducted in a sputtering atmosphere of gases at a pressure of about 0.65Pa to 3.5Pa having a nitrogen to argon ratio of about 0:50 to 20:50 and a power density of about 2 to 6 watts per square centimeter.

11. (Previously Presented) The phosphor of claim 10, wherein oxygen is added to said sputtering atmosphere.

12. (Previously Presented) The phosphor of claim 8, wherein said aluminum nitride barrier layer is deposited by atomic layer chemical vapour deposition.

13. (Previously Presented) The phosphor of claim 8, wherein said aluminum nitride barrier layer has a optical index of refraction of up to about 2.0.

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17. (Previously Presented) The phosphor of claim 1, wherein said zinc sulfo-selenide is represented by the formula ZnS_xSe_{1-x}:A where $0<x<1$ and A is an activating element.

18. (Previously Presented) The phosphor of claim 1, wherein said zinc selenide

phosphor material is represented by ZnSe:A where A is an activating element.

19. (Previously Presented) The phosphor of claim 32, wherein said transition metal activated zinc sulfide is represented by the formula ZnS:A where A is selected from manganese and terbium.

20. (Previously Presented) A phosphor laminate for use in a thick film dielectric electroluminescent display, said phosphor laminate comprising; a phosphor thin film layer selected from the group consisting of

(a) a rare earth activated alkaline earth thioaluminate;

(b) a rare earth or transition metal activated zinc selenide; and

(c) a rare earth or transition metal activated zinc sulfo-selenide,

an aluminum nitride layer provided directly adjacent a top and/or bottom side of the phosphor layer of (a), (b) and (c).

21. (Previously Presented) The laminate of claim 20, wherein said aluminum nitride barrier layer has a thickness of about 30nm to about 50nm.

22. (Previously Presented) The laminate of claim 21, wherein said phosphor thin film layer is (a) and said aluminum nitride barrier layer is provided on the top side of said phosphor thin film layer.

23. (Previously Presented) A thick film dielectric electroluminescent device constructed on a glass or glass ceramic substrate and comprising a phosphor selected from the group consisting of

(a) a rare earth activated alkaline earth thioaluminate;

(b) a rare earth or transition metal activated zinc selenide; and

(c) a rare earth or transition metal activated zinc sulfo-selenide,

wherein said phosphor film of (a), (b) and (c) is provided with an aluminum nitride barrier layer on a top and/or bottom side of the phosphor film.

24. (Previously Presented) The device of claim 23, wherein said aluminum nitride barrier layer has a thickness of about 30nm to about 50nm.

25. (Previously Presented) A method for making a stabilized phosphor laminate for use in a thick film dielectric electroluminescent device, said method

comprising

i) deposition of a phosphor selected from the group consisting of:

(a) a rare earth activated alkaline earth thioaluminate;

(b) a rare earth or transition metal activated zinc selenide; and

(c) a rare earth or transition metal activated zinc sulfo-selenide, onto a glass or glass ceramic substrate incorporating a first set of address lines and a dielectric layer;

ii) deposition of a layer of aluminum nitride on top of said phosphor film of (a)-(c); and

iii) annealing said phosphor film at a temperature of up to about 1100°C.

26. (Previously Presented) The method of claim 25, wherein said method further comprises deposition of a layer of aluminum nitride on the bottom of said phosphor film of (a), (b), and (c).

27. (Previously Presented) The method of claim 26, wherein said aluminum nitride has a thickness of about 30nm to about 50nm.

28. (Previously Presented) The method of claim 27, wherein said aluminum nitride barrier layer is deposited by sputtering.

29. (Previously Presented) The method of claim 28, wherein said sputtering is conducted in a sputtering atmosphere of gases at a pressure of about 0.65Pa to 3.5Pa having a nitrogen to argon ratio of about 0:50 to 20:50 and a power density of about 2 to 6 watts per square centimeter.

30. (Previously Presented) The method of claim 29, wherein oxygen is added to said sputtering atmosphere.

31. (Previously Presented) The method of claim 27, wherein said aluminum nitride barrier layer is deposited by atomic layer chemical vapour deposition.

32. (Previously Presented) An improved phosphor film for a thick film dielectric electroluminescent display, said phosphor film selected from the group consisting of a transition metal activated zinc sulfide; wherein said phosphor film is provided with an aluminum nitride barrier layer on a top side of the phosphor film, said

aluminum nitride barrier layer improving the stability of the interface between the phosphor film and the display; and further wherein said aluminum nitride barrier layer is about 30nm to about 50nm thick.